

HSS104

Silicon Epitaxial Planar Diode for High Speed Switching

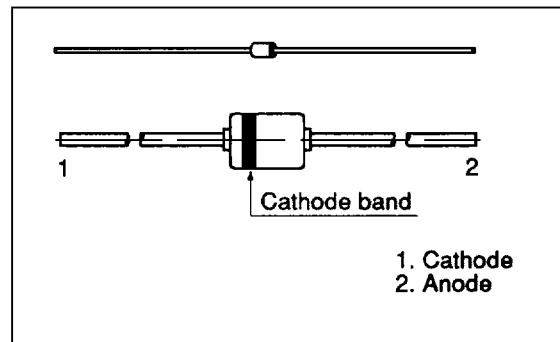
Features

- Short reverse recovery time and forward recovery time.
- Suitable for 5mm pitch high speed automatical insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Code
HSS104	Blue	MHD

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	40	V
Reverse voltage	V_R	35	V
Peak forward current	I_{FM}	300	mA
Non Repetitive peak forward surge current	I_{FSM}^*	0.4	A
Average forward current	I_o	110	mA
Power dissipation	P_d	300	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +175	$^\circ\text{C}$

* Within 1s forward surge current

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.2	V	$I_F = 100 \text{ mA}$
Reverse current	I_R	—	—	0.5	μA	$V_R = 35 \text{ V}$
Capacitance	C	—	—	3.0	pF	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$
Reverse recovery time	t_{rr}	—	—	3.0	ns	$I_F=10\text{mA}, V_R=6\text{V}, R_L=50\Omega$

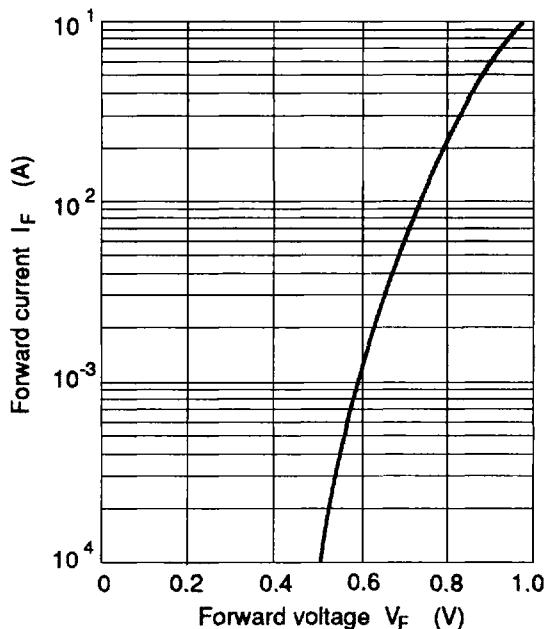


Fig.1 Forward current Vs.
Forward voltage

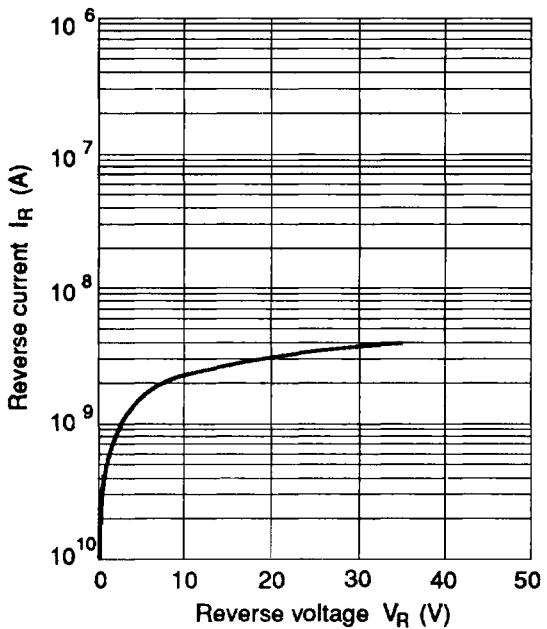


Fig.2 Reverse current Vs.
Reverse voltage

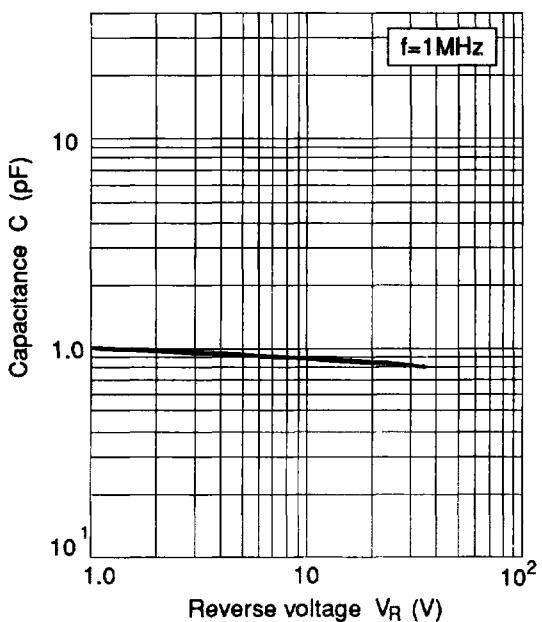


Fig.3 Capacitance Vs.
Reverse voltage